Title (en)

BASE RESISTANCE CONTROLLED MOS GATED THYRISTOR WITH IMPROVED TURN-OFF CHARACTERISTICS.

Title (de)

BASIS-WIDERSTANDS-GESTEUERTER MOS-GATE-THYRISTOR MIT VERBESSERTEM AUSSCHALT-VERHALTEN.

Title (fr)

THYRISTOR A GRILLE MOS COMMANDE PAR RESISTANCE DE BASE ET PRESENTANT DES CARACTERISTIQUES DE DESAMOR AGE AMELIOREES.

Publication

EP 0638204 A1 19950215 (EN)

Application

EP 93910724 A 19930421

Priority

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Abstract (en)

[origin: WO9322798A1] An inventive thyristor structure includes anode and cathode electrodes, with a diverter electrode being connected to the cathode electrode. A multi-layer body of semiconductor material has a first surface and includes a regenerative portion (110) operatively coupled between the anode and cathode electrodes, with a non-regenerative portion (120) being operatively coupled between the anode and diverter electrodes. The regenerative portion includes adjacent first (170), second (180), third (200) and fourth regions (240) of alternating conductivity type arranged respectively in series between the cathode and anode electrodes, wherein the cathode electrode is in electrical contact with the first region and the anode electrode is in electrical contact with the fourth region.

IPC 1-7

H01L 29/72

IPC 8 full level

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CPC (source: EP)

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See references of WO 9322798A1

Designated contracting state (EPC)

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